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► **To cite this version:**

Bin Zhao, Feng Xu, Laurent Belliard, Haijun Huang, Bernard Perrin, et al.. Sound Velocities and Elastic Moduli of Phases I and V of Silicon at High Pressures. *physica status solidi (RRL) - Rapid Research Letters*, 2019, 13 (8), pp.1900173. 10.1002/pssr.201900173 . hal-02316887

HAL Id: hal-02316887

<https://hal.science/hal-02316887>

Submitted on 7 Nov 2023

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Sound velocities and elastic moduli of phases I and V of silicon at high pressures

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Keywords: (silicon, high-pressure phases, sound velocities, elastic moduli)

Abstract

Pressure dependences of longitudinal sound velocities, in the two phases Si-I and Si-V of silicon having, respectively, cubic-diamond and primitive-hexagonal structures, are measured using the technique of picosecond laser ultrasonics adapted to samples compressed in a diamond anvil cell (DAC). For the Si-I phase, stable at atmospheric pressure, the longitudinal sound velocity along the $\langle 100 \rangle$ direction is obtained in a single crystal up to 9 GPa. In the case of the Si-V phase, the average sound velocity for an isotropic polycrystalline sample $V_{L(\text{avg})}$ is measured for the first time between 18 and 27 GPa. Above this pressure, preferred orientation of the hexagonal crystallites of Si-V with their c -axes parallel to the compressional direction in the DAC, and to the acoustic pulse propagation direction, is progressively developing thus precluding further $V_{L(\text{avg})}$ measurement. The experimental single

1 crystal elastic constants $C_{11}(P)$ and $C_{12}(P)$ of Si-I, and the shear modulus of
2 polycrystalline Si-V deduced here are in a very good agreement with our first
3 principles calculations and with the earlier results reported for Si-I.
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8 **Main text**

9
10 Silicon has come into wide use in semiconductor field and become the basic material
11 due to its chemical, physical and technical properties at atmospheric pressure. Upon
12 compression, silicon metalizes and undergoes a series of phase transitions, and thus is
13 considered as an example elemental solid in pressure-induced phase transition studies.
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15 Crystal structures, phase stability, related lattice dynamic properties were the subjects
16 of intense experimental and theoretical interest over the past decades.^[1,2,3] X-ray
17 diffraction studies indicated that the sequential structural transitions of silicon with
18 increasing pressure are as follows: cubic-diamond (Si-I) \rightarrow β -Sn (Si-II)^[4] \rightarrow *Imma*
19 (Si-XI)^[5] \rightarrow primitive-hexagonal (Si-V)^[6] \rightarrow *Cmca* (Si-VI)^[6] \rightarrow hexagonal
20 closed-packed (Si-VII)^[6] \rightarrow face-centered cubic (Si-X, up to 248 GPa)^[7]. Si-II, Si-XI
21 and Si-VI phases are stable in quite narrow pressure regions,^[8] and exist as single
22 phases in even narrower regions due to coexistence with the adjacent phases. In
23 contrast, Si-I, Si-V, Si-VII and Si-X exist as single phases in extended pressure ranges.
24
25 It was demonstrated that Si-I remains stable at $P < 9$ GPa,^[6] and, between 18 and 38
26 GPa, only Si-V was observed.^[9] While most of experimental high pressure studies on
27 silicon were focused on crystal structures of the phases, only few works dealt with
28 pressure dependences of elastic moduli of Si-I,^[10,11,12] and, to our knowledge, no
29 measurement of the shear modulus G or single crystal elastic constants C_{ij} of Si-V
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1 was reported yet.

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3 Knowledge of sound velocities of solids at high pressures allows a better
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5 understanding of their intrinsic elastic properties, especially of $G(P)$, which is very
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7 sensitive to subtle phase transitions,^[13] defects or inhomogeneities,^[14] and permits a
8
9 contrast-rich 3D tomography of non-uniform bodies.^[15] However, measurement of
10
11 sound velocities at high pressures is challenging, even using standard ultrasonic
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13 techniques or more recent synchrotron-based scattering techniques.^[16] In contrast to
14
15 standard ultrasonic techniques applicable in a limited pressure range, inelastic X-ray
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17 scattering permits measurement of longitudinal sound velocity V_L for a sample
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19 compressed in a DAC to very high pressures. However, it requires use of synchrotron
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21 radiation, large set-ups, very long counting times, and is only suited for samples
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23 containing elements with Z between 30 and 50.^[16] The related technique of nuclear
24
25 resonant inelastic X-ray scattering requires samples containing Mössbauer isotopes
26
27 and theoretical modeling in order to extract sound velocities from the recorded signals.
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29 Thus, none of the last two techniques is suitable for the acoustic measurements on
30
31 silicon samples in a DAC. At pressures above ~ 20 GPa, combination of DAC with
32
33 picosecond laser ultrasonics (PLU) provides access to sound velocities of opaque
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35 solids such as silicon.^[17,18] Recently, the PLU based on phonon imaging was
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37 demonstrated to permit extraction of a complete set of C_{ij} of Si-I compressed in a
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39 DAC.^[12] However, this method is less accurate when loading conditions become
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41 non-hydrostatic and deformations of the sample surface seriously influence the
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43 interferometric detection of the phonon imaging. Moreover, the acoustic mapping
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1 analysis requires single crystals which are difficult to preserve at ultrahigh pressures
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3 and upon phase transitions.
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6 The pump-probe technique called time-domain Brillouin scattering (TDBS) ^[19] could
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8 be potentially applied to measure $V_L(P)$ of semiconducting Si-I, below ~9 GPa, due to
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10 a relatively long optical penetration depth of the laser radiation with the wavelength
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12 $\lambda=800$ nm. However, no Brillouin oscillations with frequencies above ~78 GHz,
13
14 expected for Si at 1 atm. or higher pressures, were observed in our trial TDBS
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16 experiments. For this reason, the PLU based on the pulse-echo method was applied to
17
18 measure V_L of both Si-I and Si-V. Ultrafast acoustic pulses were generated and their
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20 arrivals detected by a conventional PLU setup equipped with a stabilized Michelson
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22 interferometer.^[20] Briefly, a mode-locked Ti:sapphire laser (MAI-TAI Spectra, $\lambda=800$
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24 nm) operating with a repetition rate of 80 MHz and a pulse width of <100 fs was split
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26 into a pump and a probe beam. The photon frequency of the pump beam was doubled
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28 to ensure an efficient generation of acoustic pulses in silicon.^[21] The beams were then
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30 focused on opposite sides of a sample with $\times 50$ microscope objectives to spots of ~2
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32 μm in diameter (**Figure 1**). The probe beam measured the transient reflectivity change
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34 of the sample surface, induced by arriving acoustic pulses, as a function of the time
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36 delay between the pump and probe beams. Three samples were studied in this work.
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38 These were single crystals of silicon having thicknesses of $h_0=9.74$ μm (subscript 0
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40 indicates values at 1 atm.) which surfaces were oriented along (001) and covered with
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42 thin metallic films on one or both sides to enhance the photon-acoustic transduction
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44 efficiency. In present work, the FeSi_{0.2} alloy and Ti were employed. Titanium is
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1 extensively used as a transducer in PLU because it exhibits strong photo-elastic
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3 coefficients in the near infrared range, when the photon energy is close to an interband
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5 transition.^[22] However, delamination precludes deposition of thick Ti-films ($>0.5 \mu\text{m}$)
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8 needed for a reliable detection of acoustic pulse arrivals, especially at high pressures
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10 when the V_L increases and the film thickness decreases. In the first trial experiments
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12 (run 1) where both sample sides were covered with the metallic films,
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14 Ti(350nm)/Si/FeSi_{0.2}(500nm), we have found that FeSi_{0.2} is well suited for acoustic
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16 pulse detection. Moreover, thick FeSi_{0.2} films could be deposited on Si without
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18 delamination. Because acoustic pulses could be generated directly and efficiently on
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20 Si using the pump beam with $\lambda=400 \text{ nm}$,^[21] samples covered with FeSi_{0.2} films on one
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22 side, FeSi_{0.2}(1 μm)/Si, were used in the runs 2 and 3. The samples were compressed in
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24 a DAC with beveled diamond anvils having culets of 300 μm in diameter. A hole of
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26 $\sim 100 \mu\text{m}$ in diameter, drilled in a steel gasket pre-indented to the thickness of $\sim 40 \mu\text{m}$,
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28 served as the sample volume. The samples were placed on one of the anvils and the
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30 remaining volume was filled with NaCl which served as a pressure transmitting
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32 medium (PTM) (Figure 1). Fluorescence of small ruby grains placed near the sample
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34 was used to measure pressure.^[23]

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37 All first-principles calculations in this work were based on the density functional
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39 theory (DFT) as implemented in the Vienna Ab-initio Simulation Package
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41 (VASP).^[24,25] The total energy per atom was evaluated with 10^{-3} meV/atom
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43 convergence accuracy, for both cubic (space group $Fd\bar{3}mO1$) and hexagonal (space
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45 group $P63/mmc$) cells containing four and two atoms, respectively. The electron-ion
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1 interactions were described by the projector augmented wave method (PAW)^[26] with a
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3 plane wave energy cutoff of 800 eV for cell optimizations, under the generalized
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5 gradient approximation (GGA) with a Perdew-Burke-Ernzerhof (PBE) exchange
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7 correlation functional.^[27] The Monkhorst-Pack scheme^[28] was used to construct
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9 k -meshes with 0.5 nm^{-1} spacing for self-consistent calculations.
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14 An example of measured transient reflectivity used to extract V_L for one of our
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16 samples is shown in Figure 1. From such a record, the V_L value was determined using
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18 the relation: $V_L=2h/\Delta t$, where Δt is duration of the acoustic pulse roundtrip in the
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20 silicon sample having thickness h . The latter was great enough to guarantee an
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22 excellent accuracy for the Δt determination ($<5 \text{ ps}$) which corresponds to the V_L
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24 uncertainty below 0.2%. The sample thickness on compression was deduced from the
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26 measured here lateral area of the sample surface S and the earlier reported equation of
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28 state (EOS), $V(P)$.^[2] At each pressure step, we recorded an optical image of the
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30 sample and used it to determine pressure dependence of the ratio $S(P)/S_0$. Dividing the
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32 known $V(P)/V_0$ for all silicon phases by our $S(P)/S_0$, we obtained the relative thickness
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34 change $h(P)/h_0$. In the case of Si-I, the obtained dependence obeyed the earlier
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36 measured EOS: $h(P)/h_0=[V(P)/V_0]^{1/3}$ which indicated that the loading conditions were
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38 close to hydrostatic and that the sample remained a single crystal till 9 GPa, close to
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40 the onset of the transition to Si-II. Above this transition, the correlation between
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42 $h(P)/h_0$ and $V(P)/V_0$ did not hold anymore thus suggesting plastic deformation of the
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44 sample due to growing non-hydrostaticity upon compression and low hardnesses of
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46 the high-pressure metallic phases of silicon. For this reason, thickness of the samples
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1 at $P > 10$ GPa was determined using the expression: $h(P) = h_0 [V(P)/V_0] [S_0/S(P)]$. We
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3 note that the $S(P)$ and, accordingly, $h(P)$ above 10 GPa was determined with the
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5 uncertainty of less than $\sim 2.5\%$, much larger than that of Δt .
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9 Our experimental V_L values for all three runs are shown in **Figure 2**. Because Si-II
10 and Si-XI coexist with the neighbor phases, and their volume ratios have not been
11 well established in the literature, further analysis of the dependences $V_L(P)$ between 9
12 and 18 GPa was not meaningful. At pressures where only Si-I is present, up to 9 GPa,
13 the measured $V_L(P)$ corresponds to that along $\langle 100 \rangle$. This is supported by the
14 comparison with the value $V_{L\langle 100 \rangle}(P)$ we calculated for the same direction in a single
15 crystal of Si-I (Figure 2). Combining our $V_{L\langle 100 \rangle}(P)$ and the EOS,^[2] providing mass
16 density $\rho(P)$ and bulk modulus $B(P)$, we derived pressure dependences of $C_{11}(P)$ and
17 $C_{12}(P)$ using the well-known expressions: $C_{11} = \rho V_{L\langle 100 \rangle}^2$ and $C_{12} = (3B -$
18 $C_{11})/2$. In **Figure 3** we compare our experimental and theoretical $C_{11}(P)$ and $C_{12}(P)$
19 with the earlier experimental and theoretical results.^[10,11,12] An overall good
20 agreement is found, even though our GGA values are $\sim 10\%$ lower than those
21 calculated within the local density approximation (LDA).
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45 At pressures where only Si-V exists, between 18 GPa and 38 GPa, our measured $V_L(P)$
46 increases slowly with compression up to ~ 27 GPa. This dependence agrees with the
47 $V_{L(\text{avg})}(P)$ we calculated for a polycrystalline sample of Si-V with randomly oriented
48 grains. The value of $V_{L(\text{avg})}(P)$ is given by the expression: $V_{L(\text{avg})} = \sqrt{(3B + 4G)/3\rho}$
49 where the isotropic moduli $B(P)$ and $G(P)$ were derived from our calculated $C_{ij}(P)$ and
50 $\rho(P)$ using the Voigt-Reuss-Hill approximation. This observation indicated that up to
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1 ~27 GPa the sample of Si-V was texture free. Applying the inverse equation $G =$
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3 $3[\rho V_{L(avg)}^2 - B]/4$ to our experimental data-points and the earlier measured $\rho(P)$
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5 and $B(P)$, the experimental dependence $G(P)$ for a polycrystalline texture-free sample
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7 of Si-V was derived to 27 GPa (Figure 3).
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10 It can be recognized in Figure 2 that above ~27 GPa our experimental $V_L(P)$ increases
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12 much faster with pressure than below and strongly deviates from our theoretical
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14 $V_{L(avg)}(P)$. This suggests a significant texturing of the sample of Si-V upon
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16 compression above 27 GPa. Because the measured $V_L(P)$ approaches the maximal
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18 possible value in a hexagonal single crystal of Si-V (known to be along the c -axis,
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20 $V_{L(0001)}$), we may conclude that the developing texture was characterized by a growing
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22 number of grains which c -axes oriented along the propagation direction of the sound
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24 pulses, perpendicular to the anvil culets. This observation agrees with an earlier XRD
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26 work where strong changes in the intensity of the (001) and (100) peaks of Si-V were
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28 recognized at similar pressures.^[7] We also show in Figure 2 $V_L(P)$ derived for the
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30 mixed phase region using our $S(P)/S_0$, an earlier EOS and the same equation
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32 $h(P)=h_0[V(P)/V_0][S_0/S(P)]$. Here, we assumed that above ~10 GPa the sample
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34 contained Si-II and the following Si-XI phases only. This explains the sudden
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36 step-like decrease in $V_L(P)$ which should not appear in the case of an extended two
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38 phase region. These data were not further treated due to the absence of such
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40 information and are presented here only for completeness.
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55 In conclusion, we investigated experimentally and theoretically pressure dependences
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57 of the longitudinal sound velocities and elastic moduli of Si-I and Si-V. Under
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1 compression, the starting single crystals of Si-I underwent phase transitions and
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3 polycrystalline phases with small randomly orientated grains appeared. After the three
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6 phase transitions, the samples of Si-V could be regarded as elastically isotropic. For
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8
9 the Si-I phase, the measured $V_L(P)$ corresponds therefore to that along the $\langle 100 \rangle$
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11 direction, $V_{L\langle 100 \rangle}(P)$. For Si-V, the measured $V_L(P)$ corresponds to that of an isotropic
12
13 polycrystalline body $V_{L(\text{avg})}(P)$ but only below 27 GPa. The dependences $C_{11}(P)$ and
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15 $C_{12}(P)$ of Si-I, we derived from the experimental $V_{L\langle 100 \rangle}(P)$ using the earlier measured
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17 EOS, are in a very good agreement with previously published data and with our
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19 calculations. More important, we measured for the first time $V_L(P)$ and $G(P)$ for
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21 polycrystalline Si-V between 18 GPa and 27 GPa. Above 27 GPa, we observed
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23 texturing of the polycrystalline Si-V whose grains preferably oriented with their
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25 c -axes along the compressional direction in the DAC.
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34 **Acknowledgements**

35 The authors acknowledge financial support from NSFC (projects No.41504070 and
36 No.41874103) and CSC (File No.201606955092). We would like to thank L. Becerra
37 for sample preparation; E. Peronne for experimental assistance; Y. Wu and X. Liu for
38 fruitful discussion. We acknowledge access to the cluster MAGI of University Paris
39 13 and N. Greneche for this support.
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44 Received: ()

45 Revised: ()

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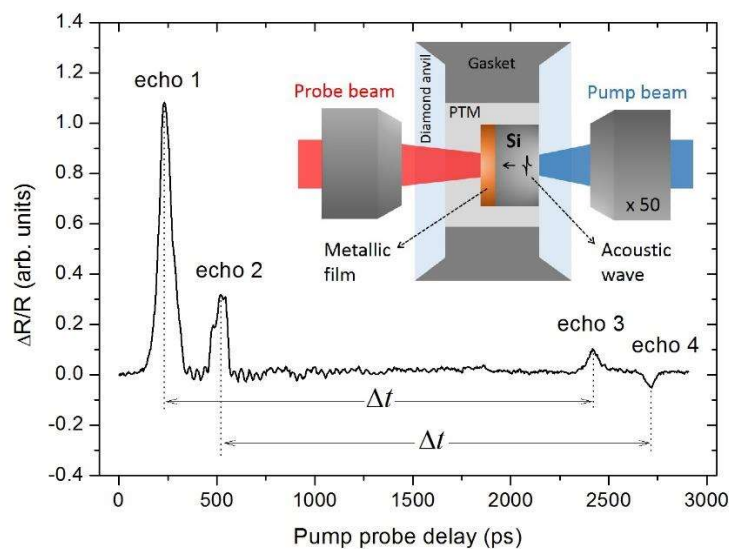
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1 **Figure 1.** Relative change of reflectivity of the sample surface as a function of
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3 pump-probe delay recorded in the run 2 at $P=6.3$ GPa. The acoustic pulse generated
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5 on the silicon side propagated in the sample and reflected from different interfaces.
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7 The echo 1 corresponds to the first arrival of the pulse on the opposite side. A part of
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9 it, reflected at the interface $\text{FeSi}_{0.2}$ (1 μm thick film)/NaCl, returns as echo 2 after the
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11 roundtrip in the $\text{FeSi}_{0.2}$ film. The time intervals Δt between echoes 1 and 3 as well as
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13 echoes 2 and 4 correspond to the pulse roundtrip in silicon. The polarity of different
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15 echoes can be explained by acoustic reflectivity at the interfaces of the sample
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17 materials with different acoustic impedances:^[20] the lowest one for NaCl, followed by
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19 Si and $\text{FeSi}_{0.2}$, and the highest for diamond. Brillouin oscillations,^[19] visible after the
20
21 arrival of the echo 1, result from interferences of the probe beam reflected from
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23 stationary surfaces and from the leaky acoustic pulse propagating in NaCl, used as the
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25 PTM. Inset: schematic representation of the sample inside a DAC. The pump beam is
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27 focused on the Si side while the probe beam on the $\text{FeSi}_{0.2}$ side.
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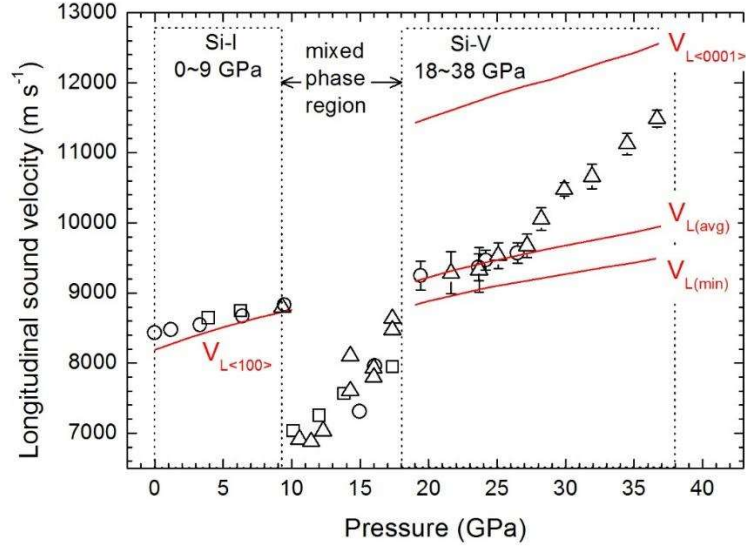


Figure 2. Longitudinal sound velocities of silicon as a function of pressure. The left and right framed ranges bracket pressures where only Si-I (0-9 GPa) and Si-V (18-38 GPa) exist. In the mixed phase region, the Si-I/Si-II, Si-II/Si-XI and Si-XI/Si-V may coexist (see text). The experimental data for the runs 1, 2 and 3 are shown by open circles, squares and triangles, respectively. For the pure Si-I region, the experimental uncertainties in V_L are smaller than the symbols. Results of our first-principles calculations are presented by solid red lines: $V_{L\langle 100 \rangle}$ is the sound velocity along $\langle 100 \rangle$ in Si-I, $V_{L\langle \min \rangle}$ and $V_{L\langle 0001 \rangle}$ are the minimal and maximal values in a hexagonal single crystal of Si-V where $V_{L\langle 0001 \rangle}$ corresponds to the velocity along the c -axis, $V_{L\langle \text{avg} \rangle}$ is that derived for polycrystalline Si-V using our theoretical $C_{ij}(P)$, $\rho(P)$ and the Voigt-Reuss-Hill approximation.

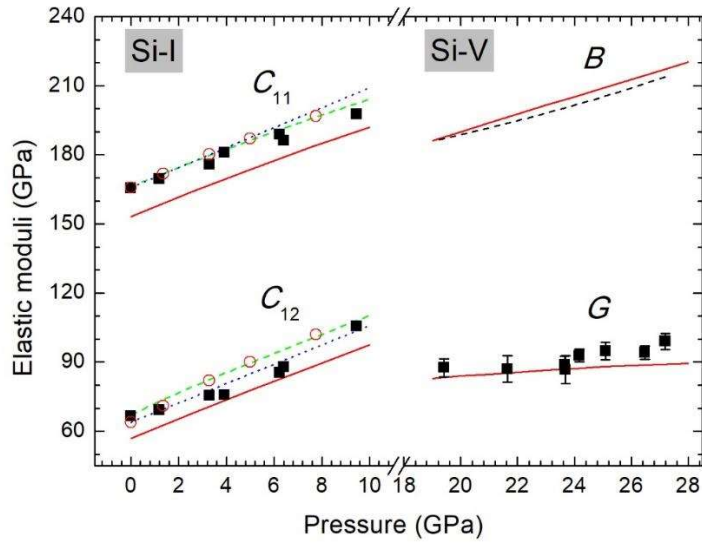


Figure 3. Pressure dependences of elastic moduli of the Si-I and Si-V phases. C_{11} and C_{12} indicate the corresponding single crystal elastic constants of Si-I. Our measured values (solid black squares) are compared with the earlier ones obtained by the phonon imaging method (open red circles)^[12] and by a traditional ultrasonic technique (dotted blue lines).^[10] Our *ab-initio* results within GGA (solid red lines) are compared with the earlier predictions within LDA (dashed green lines).^[11] Above 18 GPa, the solid black squares represent $G(P)$ of polycrystalline Si-V measured here and the dashed black line $B(P)$ ^[2] measured earlier. Our theoretical $B(P)$ and $G(P)$ are represented by solid red lines.